Pb Free Plating Product

HBR1020CJR

10.0 Ampere Heatsink Tandem Polarity Schottky Half Bridge Rectifier

Features

- Matured HMBR SKY technology
- Internal ceramic insulated package outline
- High current capability
- Low reverse leakage current
- High surge current capability

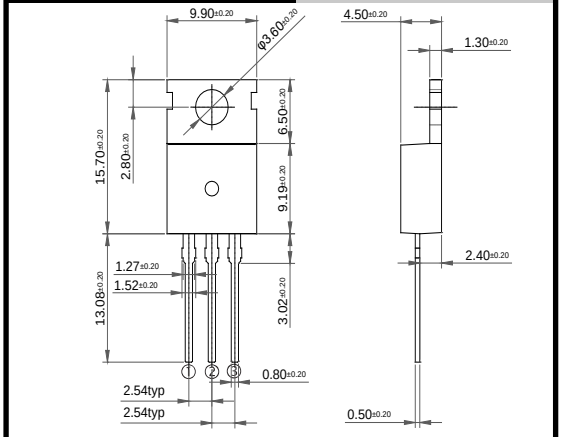
Application

- Inverters,Free Wheeling and Polarity Protection
- High Frequency SMPS,Telecom SMPS and UPS
- Car Audio Amplifiers and Sound Device Systems etc..

Mechanical Data

- Case: Heatsink TO-220CS internal ceramic insulated
- Epoxy: UL 94V-0 rate flame retardant
- Terminals: Solderable per MIL-STD-202 method 208
- Polarity: As marked on diode body
- Mounting position: Any
- Weight: 2.2 gram approximately

TO-220CS Unit:mm



$I_{F(AV)}$	10A
V_{RRM}	200V(2x100V)
T_j	175 ℃
$V_{F(max)}$	0.70V（@Tj=125℃）

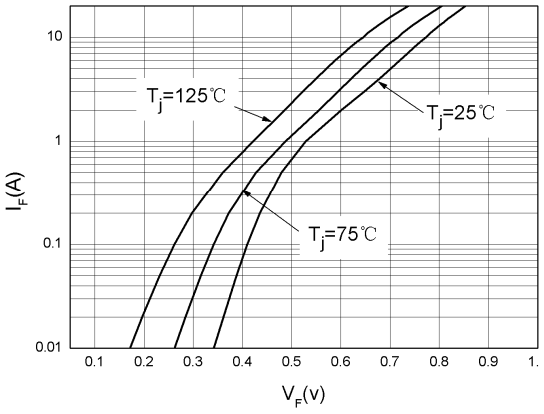
ABSOLUTE RATINGS (Tc=25℃)

Symbol	Characteristics		Maximum Ratings	Unit
V_{RRM}	Repetitive Peak Reverse Voltage	Per Device(2x100V) (Series Connection)	200	V
V_{DC}	Maximum DC Blocking Voltage	Per Diode	100	V
$I_{(AV)}$	Maximum Average Forward Rectified Current @T_C=150°C		10	A
I_{FSM}	Peak Forward Surge Current 8.3ms Single Half-Sine-Wave Superimposed On Rated Load (JEDEC METHOD)		200	A
V_F	Maximum Forward Voltage (Note 1)	@I_F=10A @T_J=25°C @I_F=10A @T_J=125°C	0.85 0.70	V V
I_R	Maximum DC Reverse Current At Rated DC Blocking Voltage	@T_J=25°C @T_J=125°C	10 5	uA mA
$R_{th(j-c)}$	Thermal Resistance from Junction to Case (Note 2)		1.9	°C/W
T_J	Operating Temperature Range		-55 to +175	°C
T_{STG}	Storage Temperature Range		-40 to +150	°C

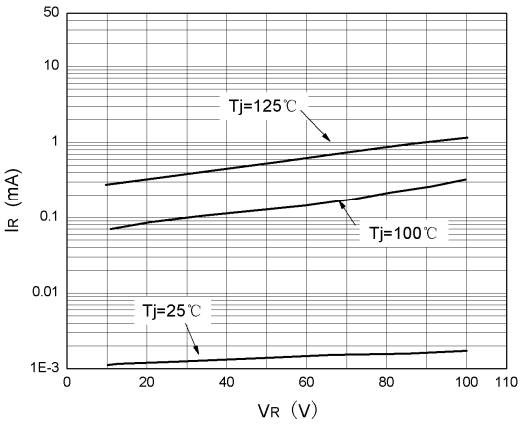
NOTE: 1. 300us Pulse Width, Duty Cycle 2%.
2. Thermal Resistance Junction To Case.
Measured At 1.0MHz And Applied Reverse Voltage Of 4.0V DC.

ELECTRICAL CHARACTERISTICS (curves)

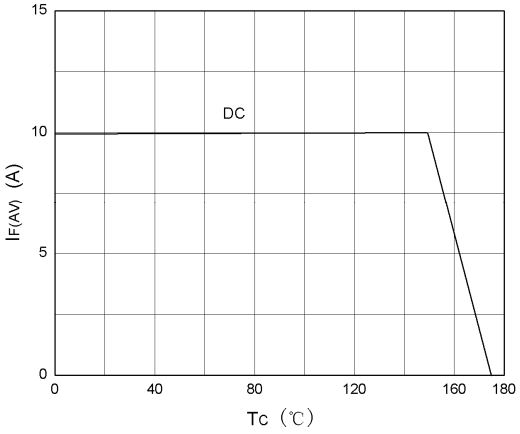
I_F vs V_F



I_R vs V_R



$I_{F(AV)}$ vs T_C (Per Diode)



C_T vs V_R (Per Diode)